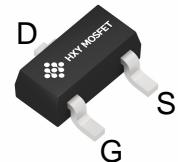




Description

The HXY2N10I uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23

General Features

$V_{DS} = 100V$ $I_D = 2.2A$

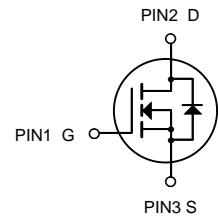
$R_{DS(ON)} < 286m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY2N10I	SOT-23	MA4	3000

Absolute Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	2.2	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ 10V	1.4	A
I_{DM}	Pulsed Drain Current	8.8	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2.3	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient	54	°C/W



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =2A	-	220	286	mΩ
		V _{GS} =4.5V, I _D =1A	-	223	312	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	321	-	pF
C _{oss}	Output Capacitance		-	21	-	pF
C _{rss}	Reverse Transfer Capacitance		-	15	-	pF
Q _g	Total Gate Charge		-	5.3	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V, I _D =2A, V _{GS} =10V	-	1.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.7	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =1A, R _{GEN} =3Ω, V _{GS} =10V	-	14	-	ns
t _r	Turn-on Rise Time		-	54	-	ns
t _{d(off)}	Turn-off Delay Time		-	18	-	ns
t _f	Turn-off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	2.2	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	8.8	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =2.2A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

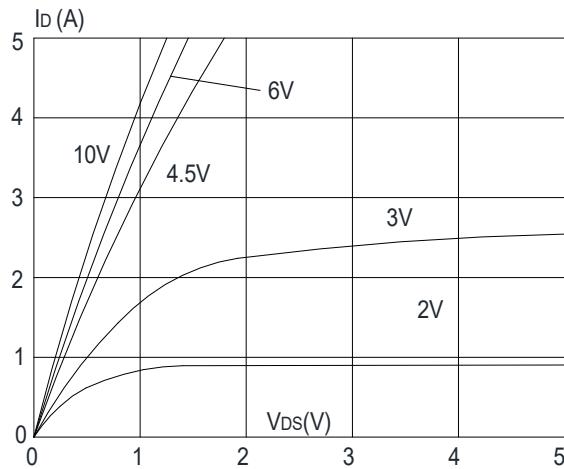


Figure 2: Typical Transfer Characteristics

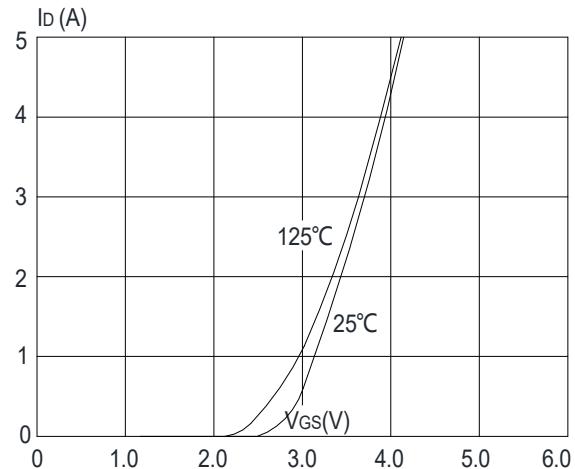


Figure 3: On-resistance vs. Drain Current

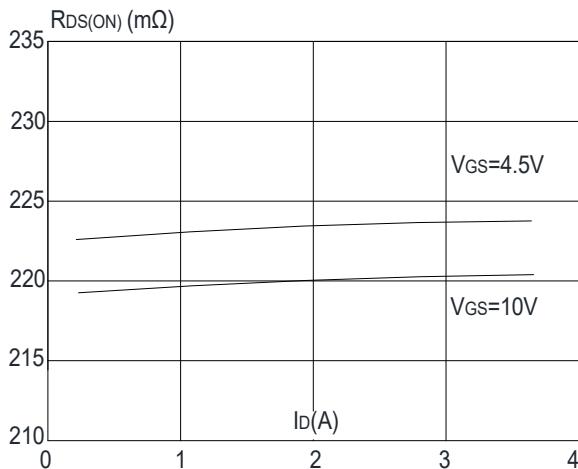


Figure 4: Body Diode Characteristics

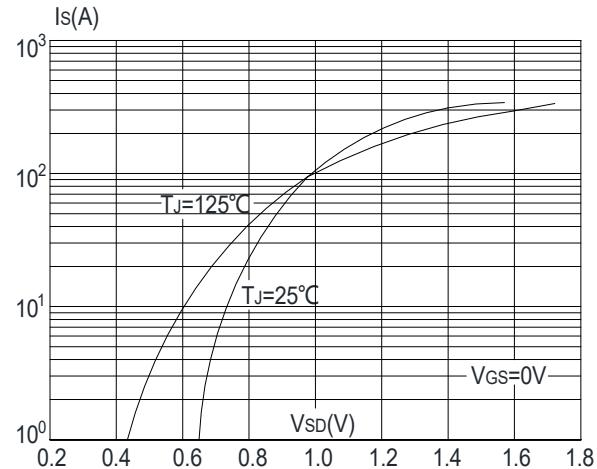


Figure 5: Gate Charge Characteristics

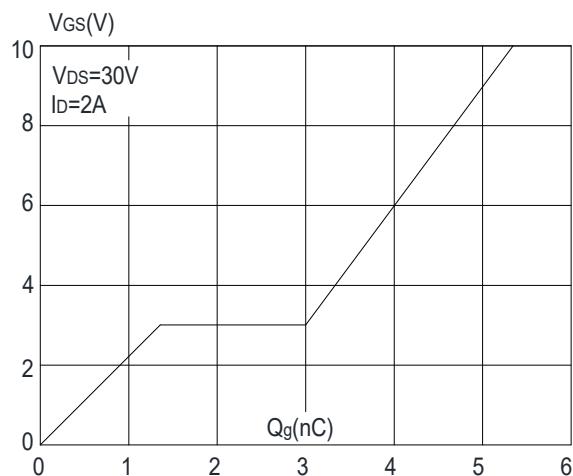


Figure 6: Capacitance Characteristics

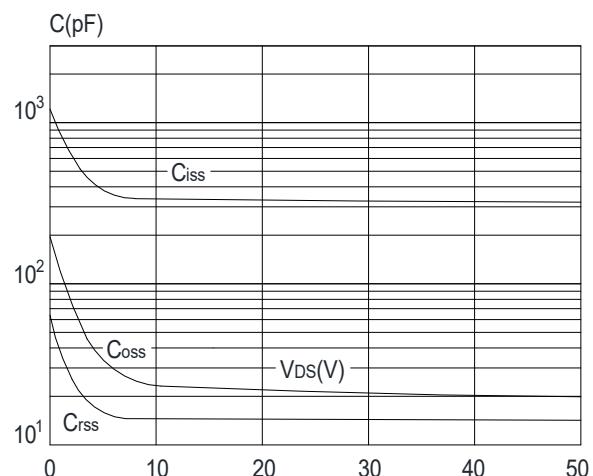




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

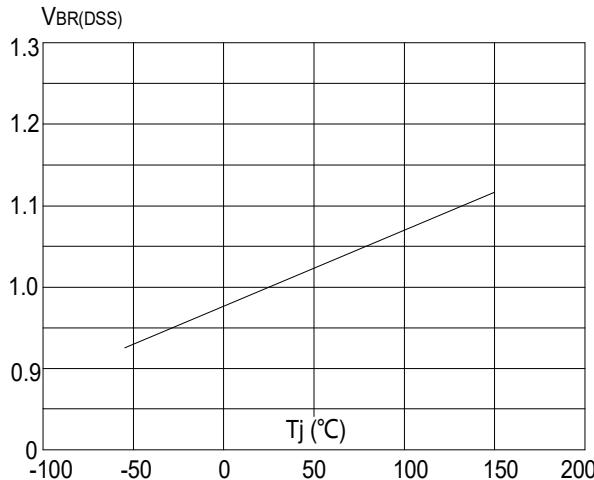


Figure 8: Normalized on Resistance vs. Junction Temperature

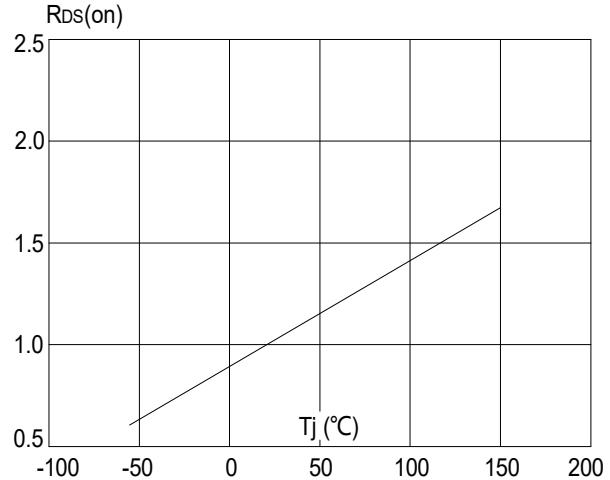


Figure 9: Maximum Safe Operating Area

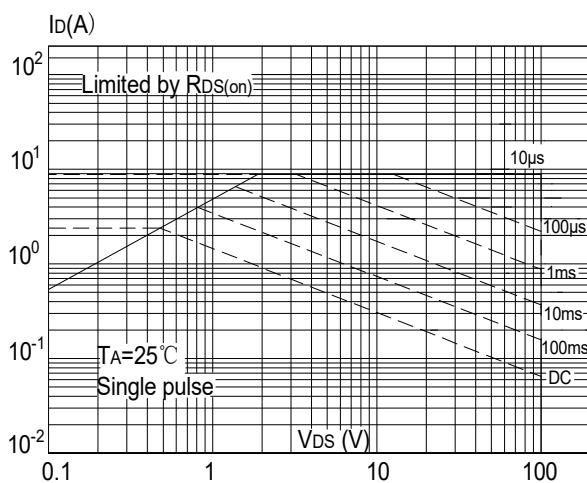


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

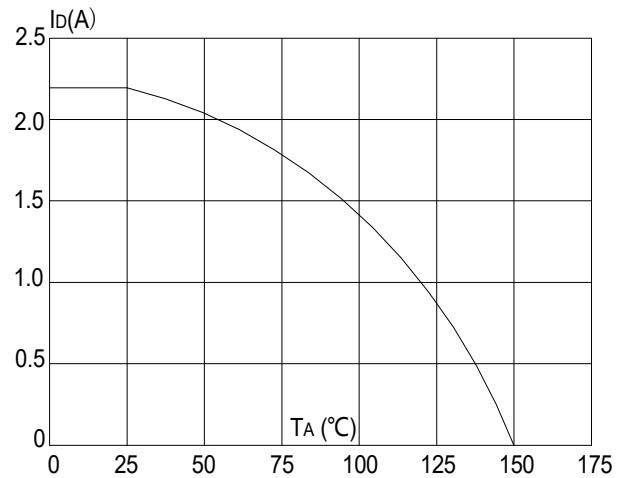
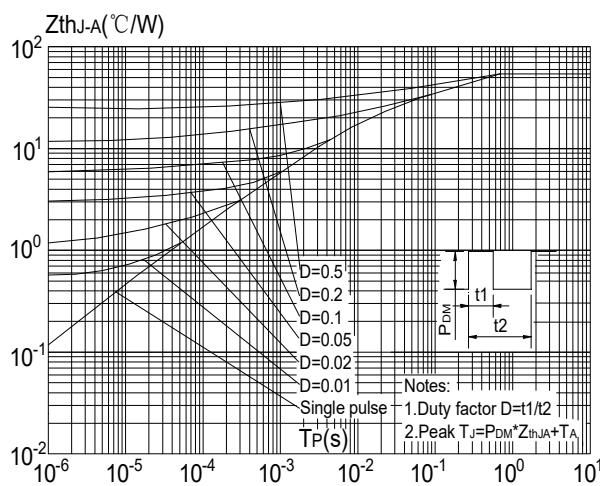


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





Test Circuit

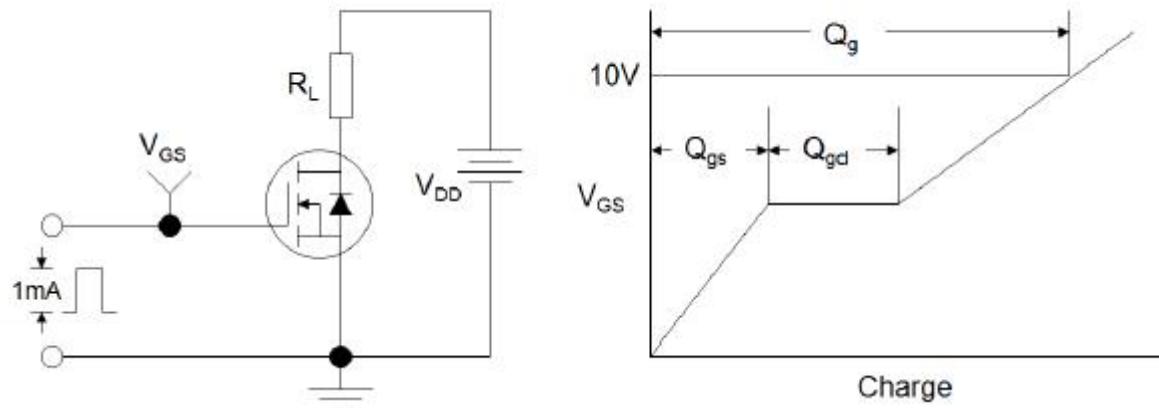


Figure 1: Gate Charge Test Circuit & Waveform

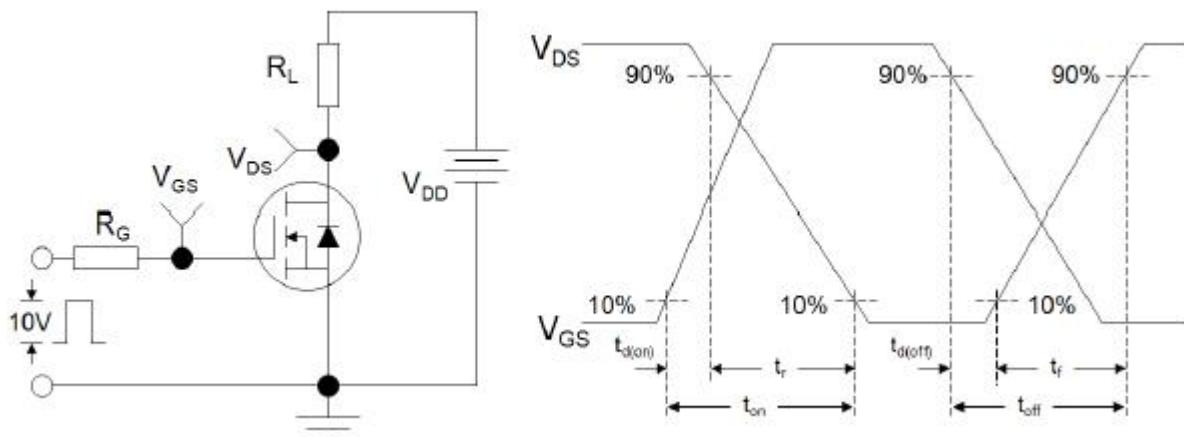


Figure 2: Resistive Switching Test Circuit & Waveforms

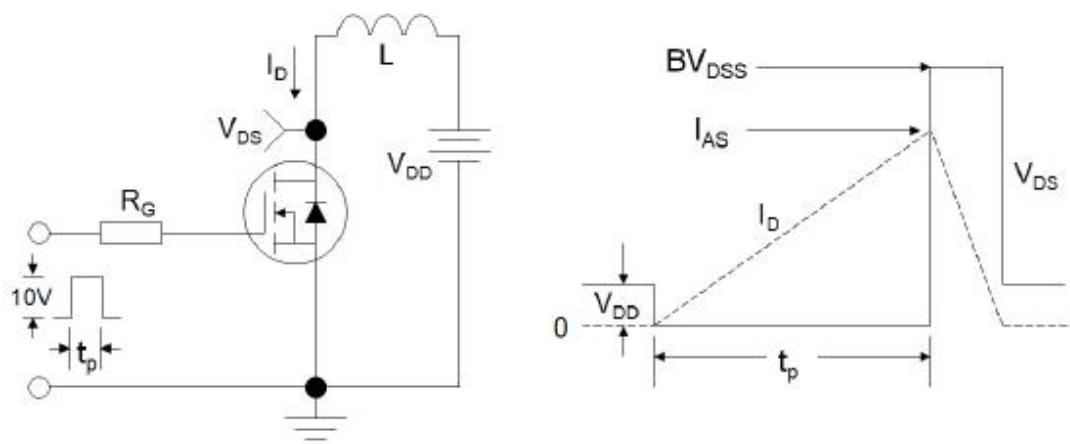
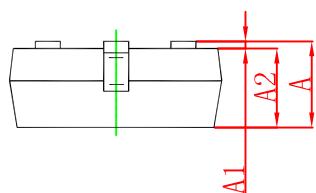
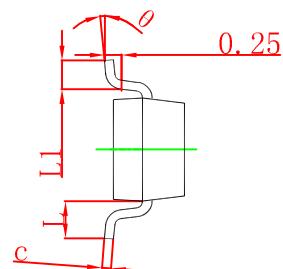
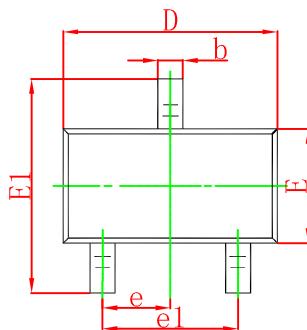


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

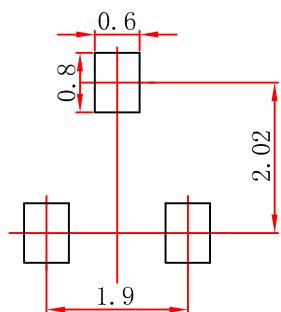


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.



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